

1-Line Uni-directional ESD Protection Diode

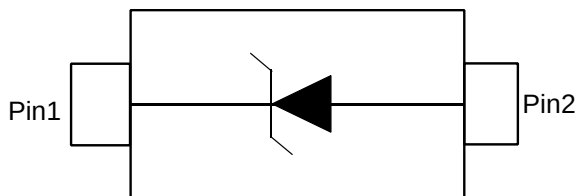
Description

Unidirectional ElectroStatic Discharge(ESD) protection diode in a SOD323 plastic package designed to protect one transmission or data line from the damage caused by ESD and other transient These surge protection diodes are designed for applications requiring transient over voltage protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. These devices are ideal for situations where board space is at a premium.

Features

- Uni-directional ESD protection of one line
- Reverse stand-off voltage: 30V Max
- Low leakage current: nA Level
- Response time is typically < 1 ns
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 7A (8/20 μs)
- RoHS Compliant

Schematic and Pin Configuration



SOD-323 (Top View)

Circuit Schematic

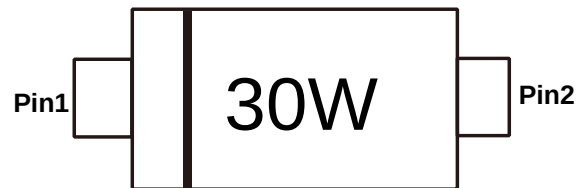
Mechanical Characteristics

- Package: SOD-323
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 1 per J-STD-020
- Marking Information: See Below

Applications

- Cell Phone Handsets and Accessories
- Microprocessor based equipment
- Personal Digital Assistants (PDA'S)
- Wireless Systems
- Notebooks,Desktops,and Servers

Marking Information



30W = Device Marking Code

Ordering Information

Part Number	Shipping	Reel Size
PSD30	3000/Tape &Reel	7 inch

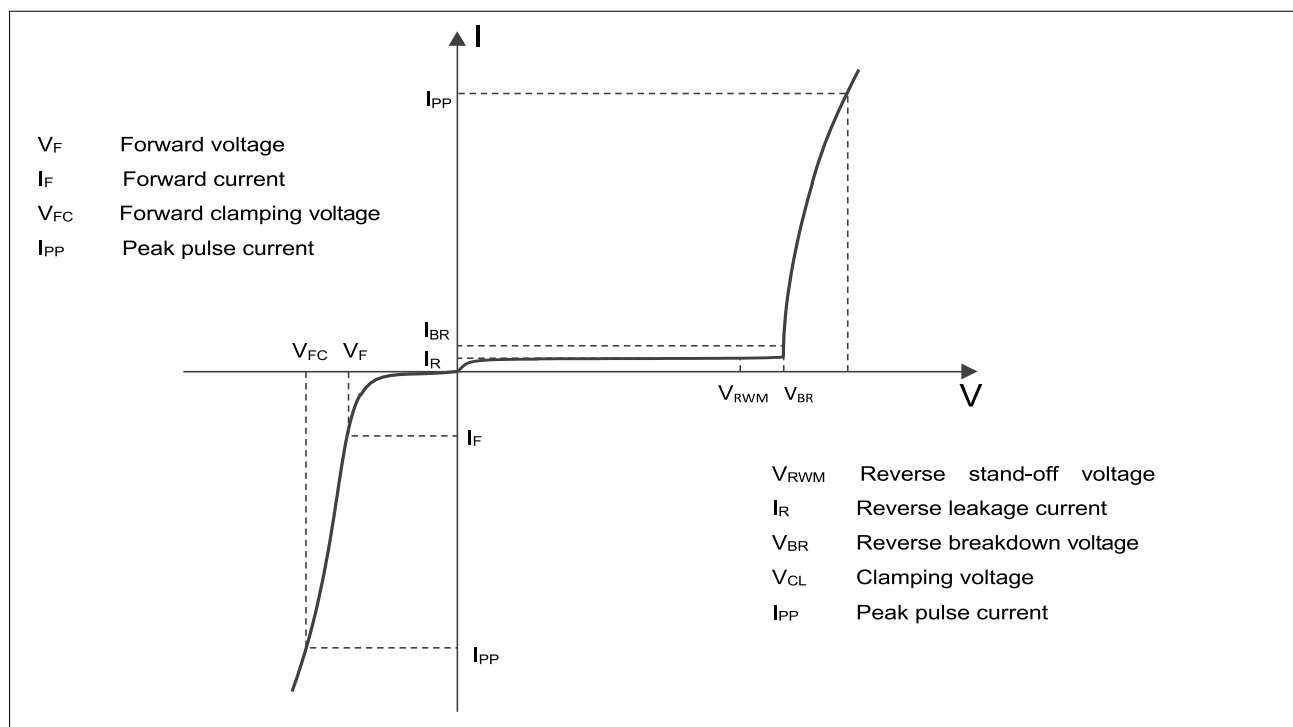
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	P_{PK}	350	W
Peak Pulse Current (8/20 μs)	I_{PP}	7	A
ESD per IEC 61000-4-2 (Air)	V_{ESD}	± 30	kV
ESD per IEC 61000-4-2 (Contact)		± 30	kV
Lead temperature	T_L	260	$^{\circ}\text{C}$
Junction Temperature	T_J	125	$^{\circ}\text{C}$
Operating Temperature Range	T_{OP}	$-40 \sim +125$	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	$-55 \sim +150$	$^{\circ}\text{C}$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

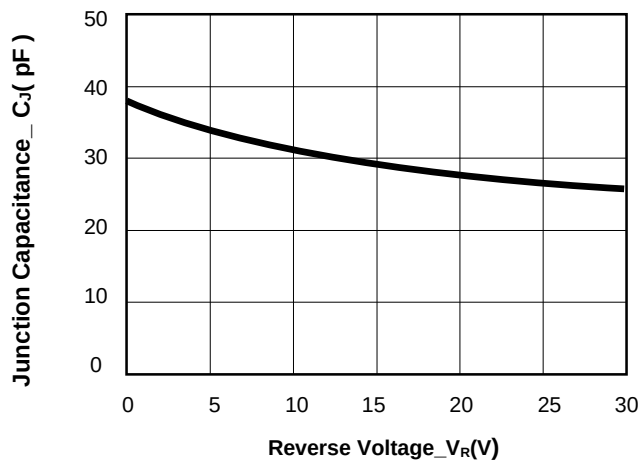
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			30	V	
Reverse Breakdown Voltage	V_{BR}	31		35	V	$I_T = 1\text{mA}$
Reverse Leakage Current	I_R			0.1	μA	$V_{RWM} = 30\text{ V}$
Forward Voltage	V_F			0.9	V	$I_F = 10\text{mA}$
Clamping Voltage	V_C			35	V	$I_{PP} = 1\text{A}$ (8/20 μs pulse)
Clamping Voltage	V_C			50	V	$I_{PP} = 7\text{A}$ (8/20 μs pulse)
Junction Capacitance	C_J		37	42	pF	$V_R = 0\text{V}$, $f = 1\text{MHz}$

Electrical characteristics ($T_A = 25^\circ\text{C}$, unless otherwise noted)

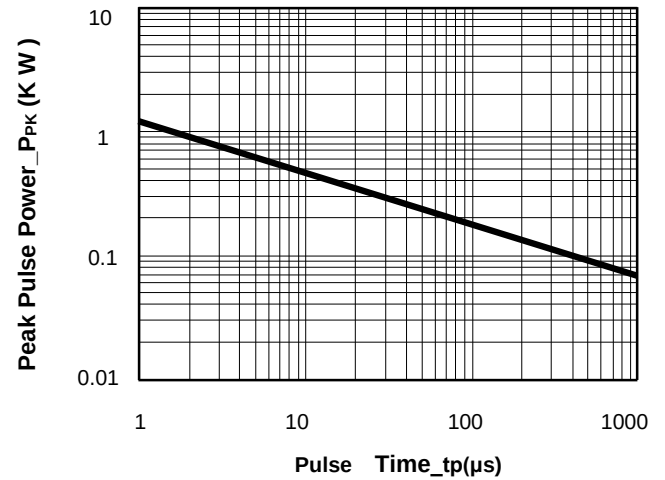


Definitions of electrical characteristics

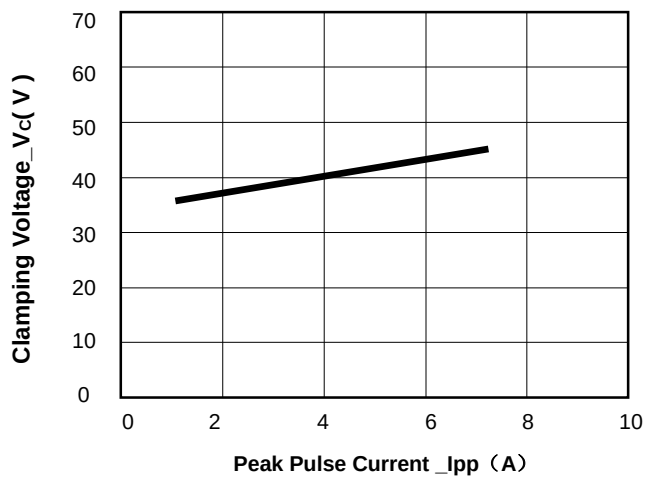
Typical Performance Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise Specified)



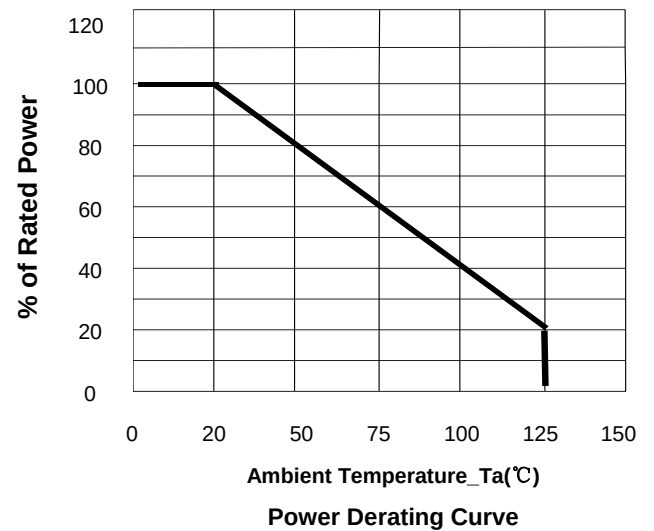
Junction Capacitance vs. Reverse Voltage



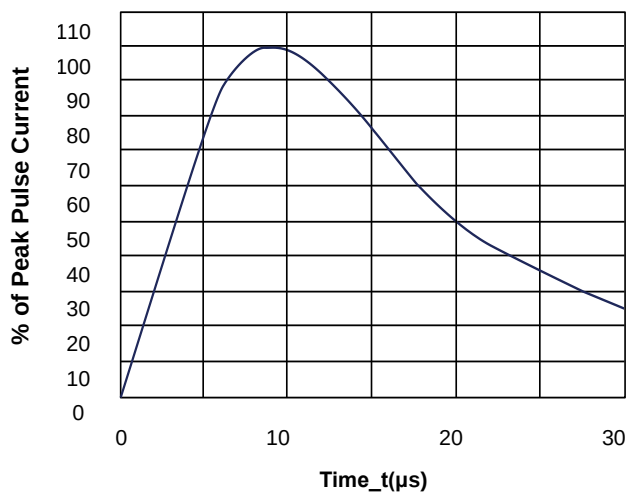
Peak Pulse Power vs. Pulse Time



Clamping Voltage vs. Peak Pulse Current

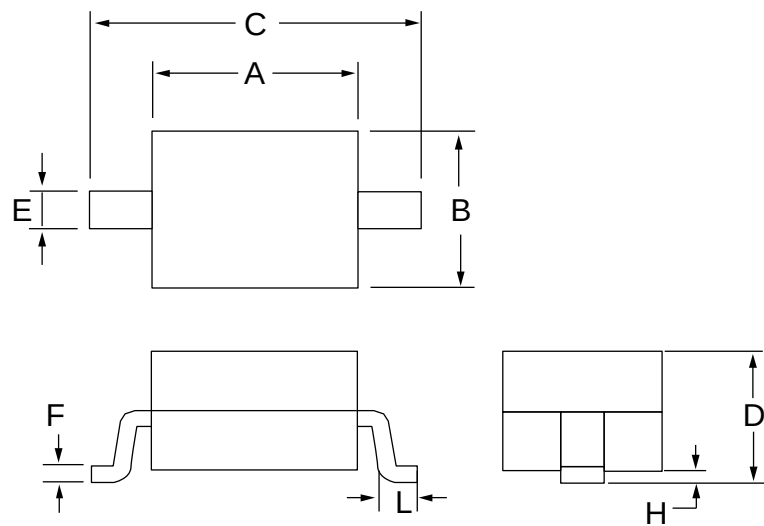


Power Derating Curve



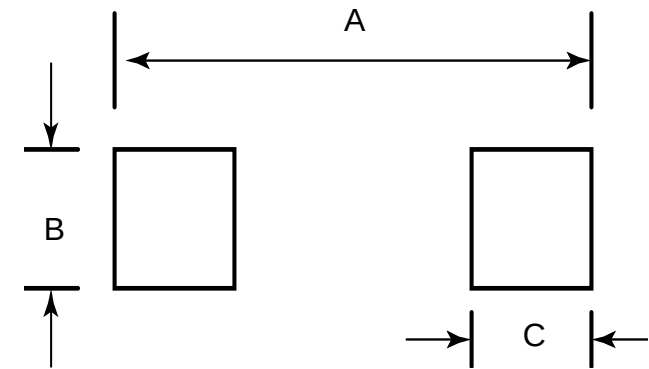
8/20 μs Pulse Waveform

SOD-323 Package Outline Drawing



SYM	DIMENSIONS				
	MILLIMETERS			INCHES	
	MIN	NOM	MAX	MIN	MAX
A	1.50	1.65	1.80	0.060	0.071
B	1.20	1.30	1.40	0.045	0.054
C	2.30	2.50	2.70	0.090	0.107
D	-		1.10	-	0.043
E	0.30		0.40	0.012	0.016
F	0.10		0.25	0.004	0.010
L	0.20		0.40	0.008	0.016
H	-		0.10	-	0.004

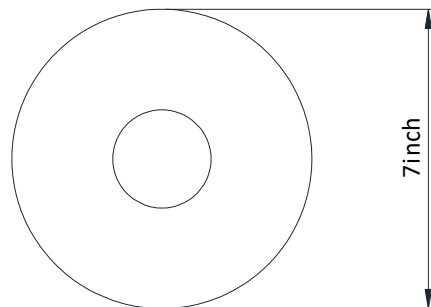
Suggested Land Pattern



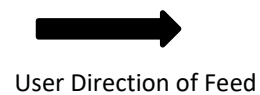
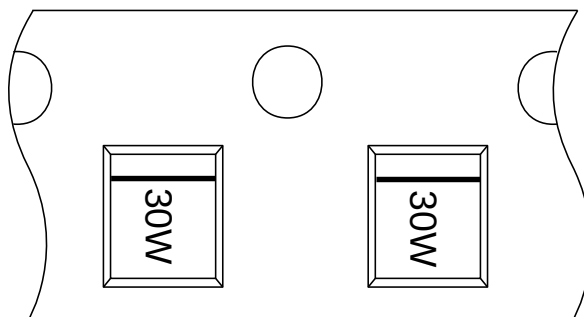
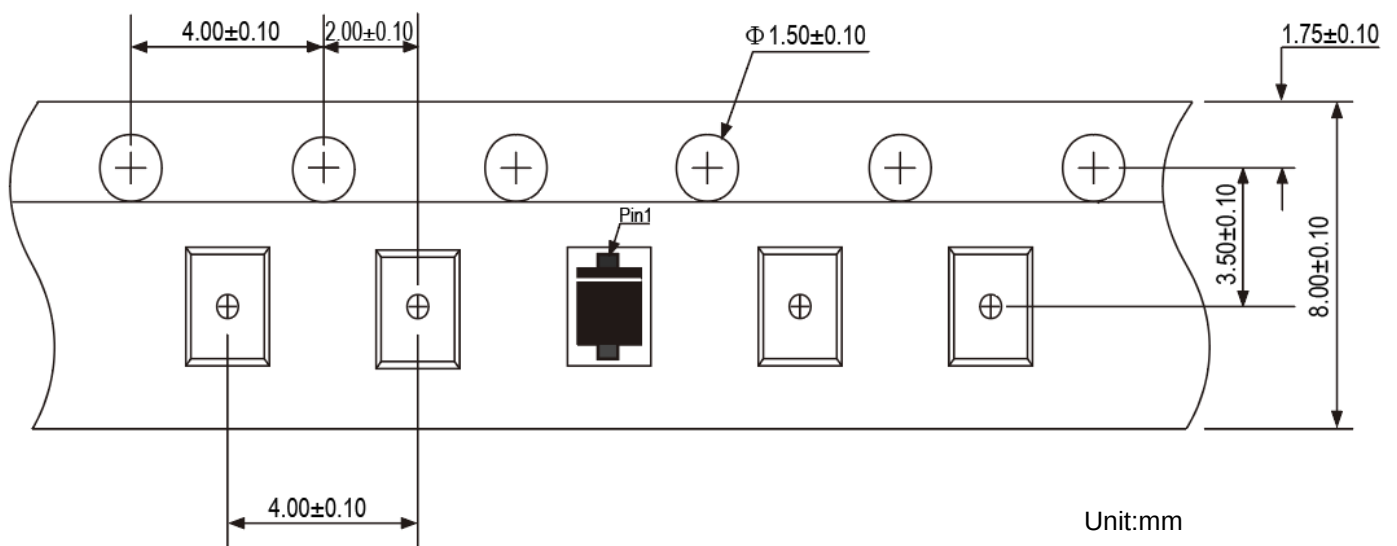
SYM	DIMENSIONS	
	MILLIMETERS	INCHES
A	3.15	0.120
B	0.80	0.031
C	0.80	0.031

TAPE AND REEL INFORMATION

Reel Dimensions



Tape Dimensions



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